

Ten new high performance MOSFETs for power management

High performance MOSFETs for DC-DC converters, OR-ing and load switching

NXP's range of 30V Trench 6 logic level MOSFETs deliver significant improvements in efficiency when used in switching power supply applications, DC-DC converters, POL converters and power OR-ing. The LFPAK package delivers high current capability and low thermal resistance in a 5mm x 6mm Power SO8 footprint making the new range of MOSFETs the natural choice for demanding power-switching applications.

Key benefits

Low PCB space, low cost

- Increased power density whilst maintaining the Power SO8 footprint
- High efficiency gains in switching power converters
- Faster switching supports higher frequencies and use of smaller inductors & capacitors
- Lower in-circuit power dissipation reduces the need for cooling
- Uses the PCB as a heatsink and reduces the need for external heatsink

Key features

- Low ON resistance R_{DS(ON)} typical from 1.2mOhm (PSMN1R7-30YL)
- ▶ Low thermal resistance Rth(jc) from 1.1 °K/W
- Low package inductance typically 1.1nH
- ▶ Footprint compatible with SO8 (5mm x 6mm)
- Low profile package height 1.1mm
- ▶ Recommended for switching frequencies up to 1MHz

Key applications

- Voltage Regulator
- Motor Control
- ► OR-ing
- Load switching
- Li-ion battery protection
- LED lighting / dimming





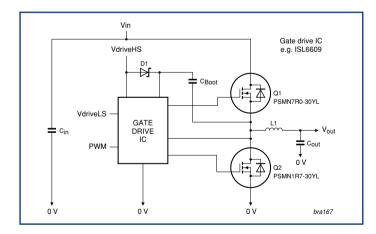
Ten new devices have been added to the PSMN 30 V range of MOSFETs from NXP. This range combines the latest silicon technology (Trench 6), with the high-performance LFPAK package, which challenges the best performing devices available in today's marketplace.

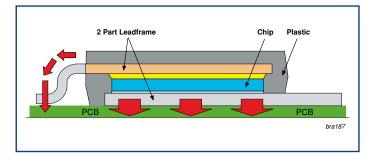
Trench 6 silicon technology provides our lowest $R_{DS(ON)}$ performance yet, at 1.2mOhm typical at V_{GS} =10V (PSMN1R7-30YL). These parts are highly suited to power OR-ing and SYNC-FET in synchronous buck-regulator applications.

Trench 6 technology also delivers low gate-charge (Q_G) and low gate-resistance (R_G) Making the devices suitable for switching frequencies typically up to 1MHz and making them ideally suited for use in high-efficiency synchronous buck regulators.

LFPAK (Loss Free PAcKage) delivers compact power in a surface-mount package. It provides superior electrical & thermal resistance as well as low inductance, while maintaining the widely accepted SO8 footprint. LFPAK is compatible with 'visual inspection' techniques unlike many other Power-SO8 devices.

The combination of Trench 6 silicon and LFPAK package delivers higher operating efficiencies, improved thermal characteristics and high power density which are essential for today's high performance power management applications.





Part Number	V _{ds}	MAX R _{DS(ON)} @ V _{GS} = 10 V	MAX R _{DS(ON)} @ V _{GS} = 4.5 V
	V	mΩ	mΩ
PSMN1R7-30YL	30	1.7	2.6
PSMN2R0-30YL	30	2.0	3.2
PSMN2R5-30YL	30	2.4	3.9
PSMN3R0-30YL	30	3.0	4.8
PSMN3R5-30YL	30	3.5	5.6
PSMN4R0-30YL	30	4.0	6.5
PSMN5R0-30YL	30	5.0	8.0
PSMN6R0-30YL	30	6.0	9.7
PSMN7R0-30YL	30	7.0	11.3
PSMN9R0-30YL	30	8.0	13.8

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